

## Description

The PSM6N30V20 uses split gate trench technology to provide excellent  $R_{DS(on)}$  low gate charge. This device is suitable for power management and high efficiency applications at high switching frequencies applications.

### MOSFET Product Summary

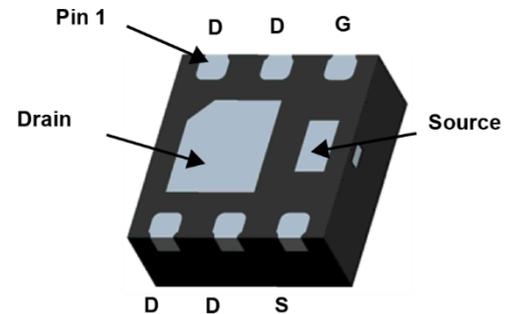
$V_{DS}(V)$	$R_{DS(on)}(m\Omega)$	$I_D(A)$
30	4.0 @ $V_{GS} = 10V$	20

## Feature

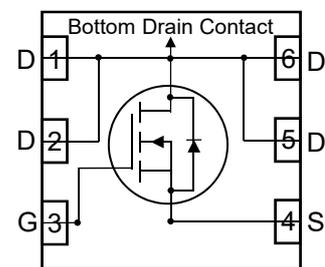
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

## Applications

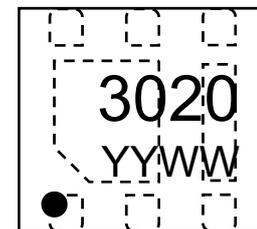
- PWM applications
- Load switch
- Power management
- DC-DC Converters
- Wireless Chargers



**DFN2020-6L**  
**(Bottom View)**



**Circuit Diagram**



**Marking (Top View)**

## Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Drain-source Voltage	$V_{DS}$	30	V
Gate-source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current	$I_D$	20	A
Pulsed Drain Current <sup>1)</sup>	$I_{DM}$	130	A
Avalanche Energy, Single Pulse	$E_{AS}$	96	mJ
Total Power Dissipation <sup>2)</sup>	$P_D$	2.4	W
Thermal Resistance Junction-to-Ambient @ Steady State <sup>2)</sup>	$R_{\theta JA}$	56	°C/W
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~+150	°C

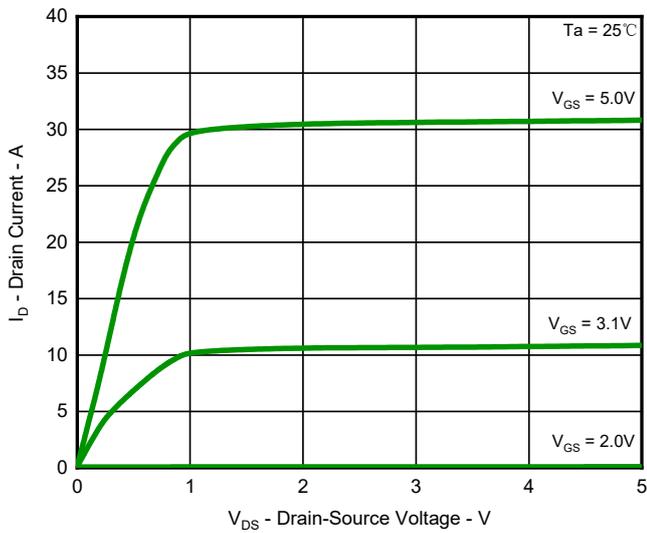
## Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30V, V_{GS} = 0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	$\pm 100$	nA
On Characteristics <sup>3)</sup>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.1	1.8	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 10A$	-	4.0	4.5	m $\Omega$
		$V_{GS} = 4.5V, I_D = 10A$	-	6.0	8.0	
Dynamic Parameters <sup>4)</sup>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15V, V_{GS} = 0V,$ $f = 1MHz$	-	1100	-	pF
Output Capacitance	$C_{oss}$		-	270	-	
Reverse Transfer Capacitance	$C_{rss}$		-	16	-	
Switching Parameters <sup>4)</sup>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 15V, I_D = 10A,$ $V_{GEN} = 10V, R_{GEN} = 3\Omega$	-	1.27	-	ns
Turn-on Rise Time	$t_r$		-	1.13	-	
Turn-Off Delay Time	$t_{d(off)}$		-	11.2	-	
Turn-Off Fall Time	$t_f$		-	4.97	-	
Total Gate Charge	$Q_g$	$V_{DS} = 15V, I_D = 10A,$ $V_{GS} = 4.5V$	-	5.5	-	nC
Gate-Source Charge	$Q_{gs}$		-	2.5	-	
Gate-Drain Charge	$Q_{gd}$		-	0.6	-	
Drain-Source Diode Characteristics						
Diode Forward Voltage <sup>3)</sup>	$V_{SD}$	$V_{GS} = 0V, I_S = 0.2A$	-	0.65	1.5	V

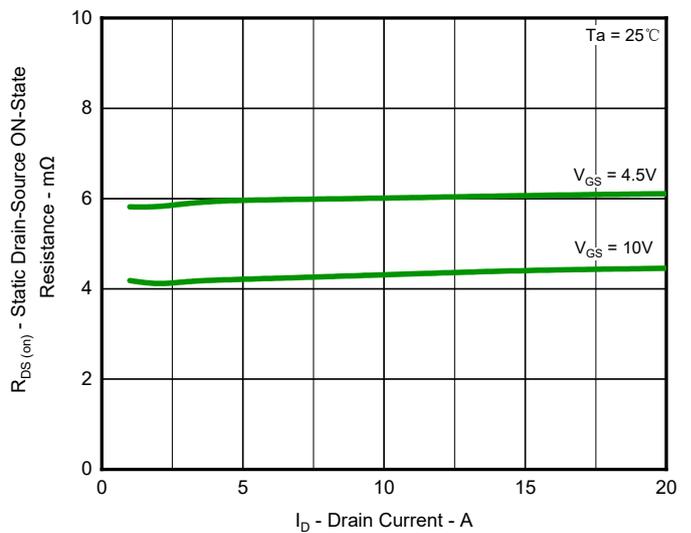
Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

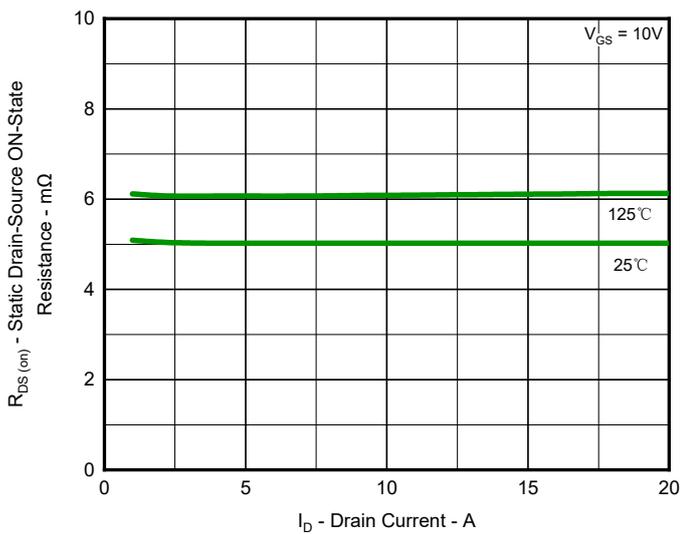
## Typical Characteristics



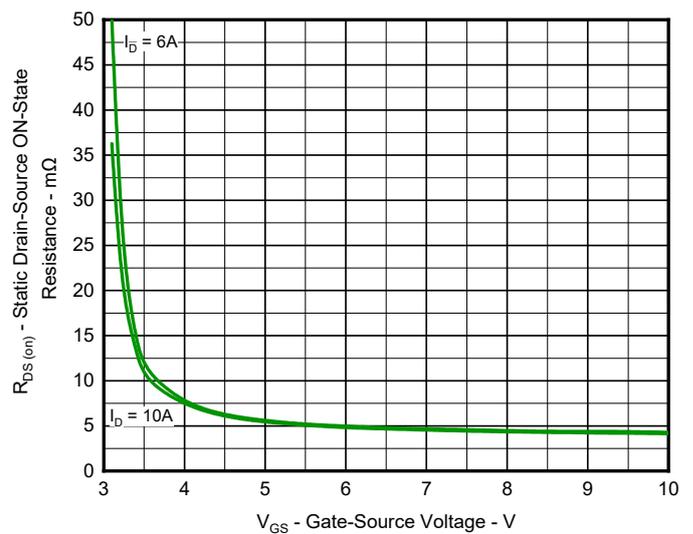
**Fig.1 Output Characteristics**



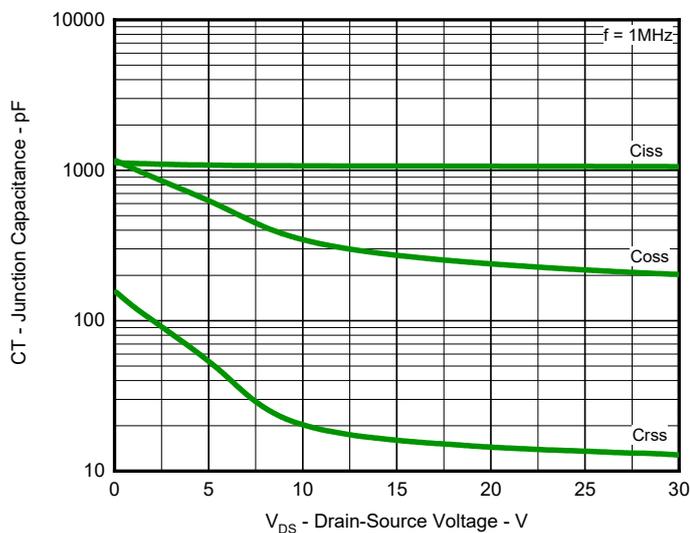
**Fig.2 On-Resistance vs. Drain Current (I)**



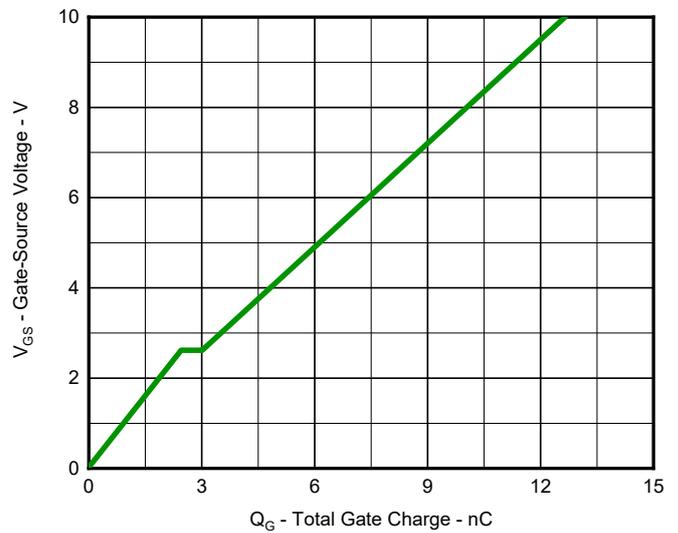
**Fig.3 On-Resistance vs. Drain Current (II)**



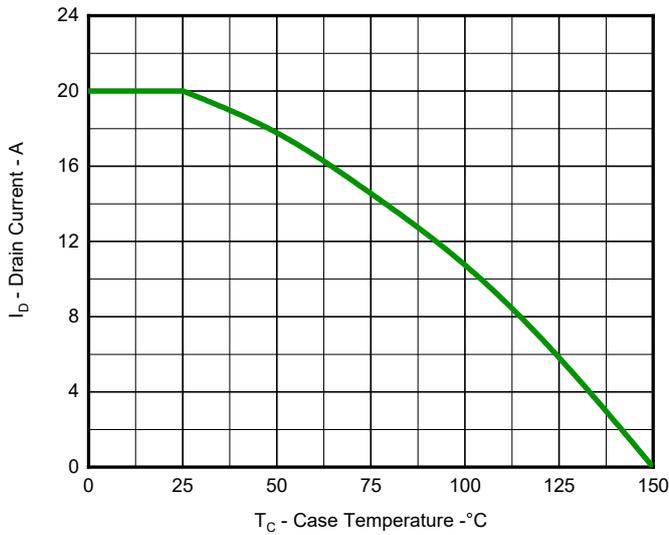
**Fig.4 On-Resistance vs. Gate-Source Voltage**



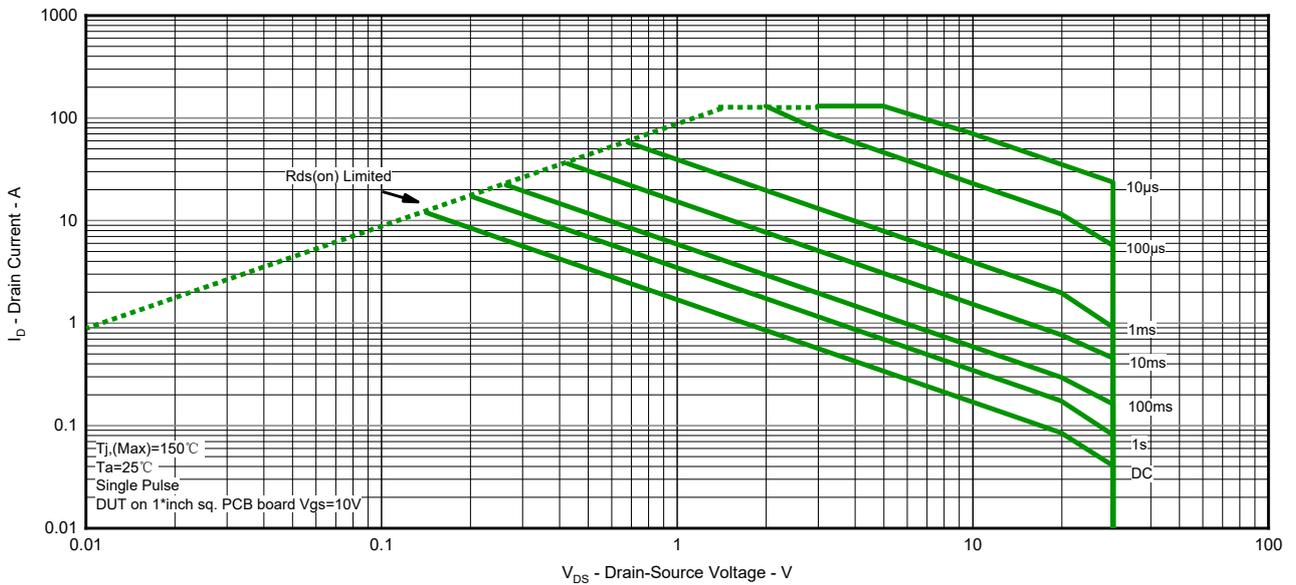
**Fig.5 Typical Junction Capacitance**



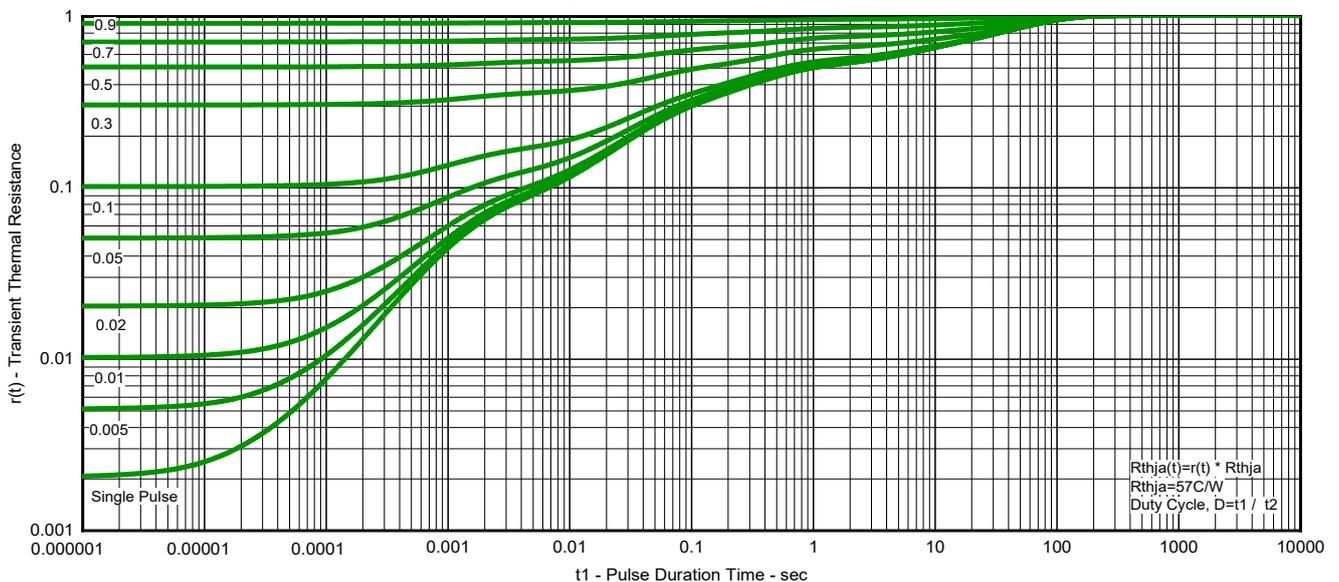
**Fig.6 Gate Charge Characteristics**



**Fig.7 Maximum Drain Current vs. Case Temperature**

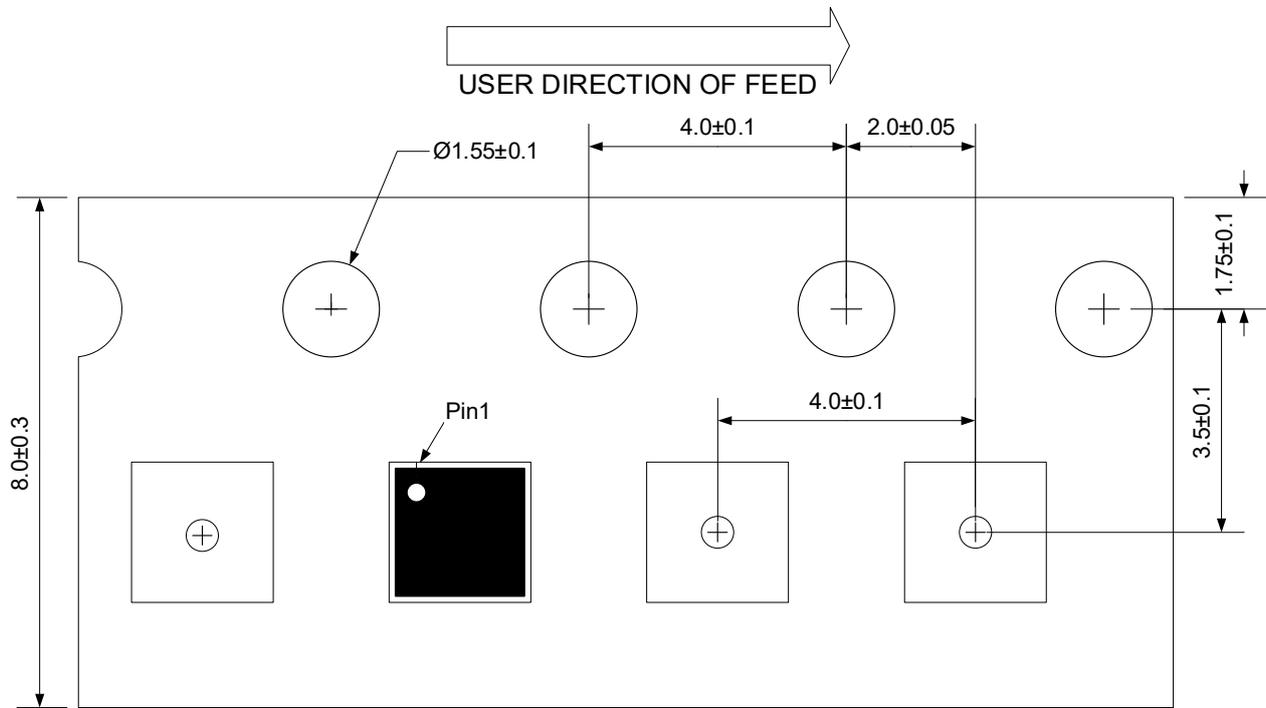


**Fig.8 Safe Operation Area**



**Fig.9 Transient Thermal Resistance**

Load with information

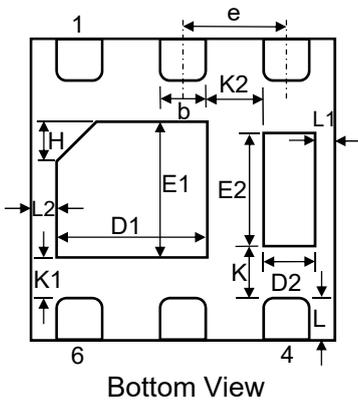
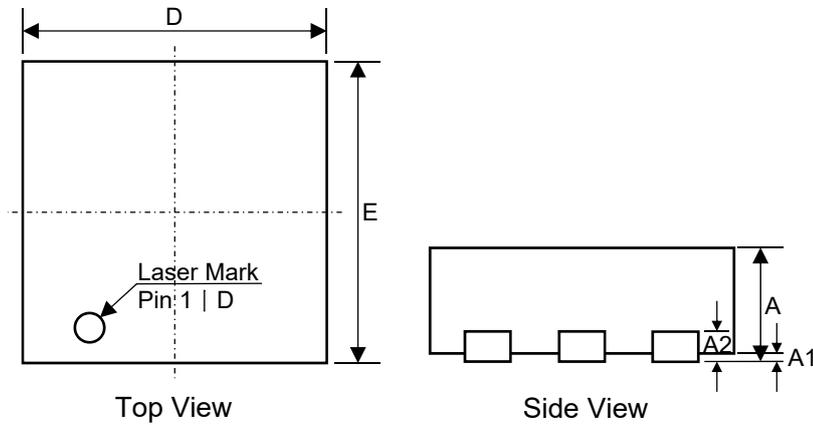


Unit:mm

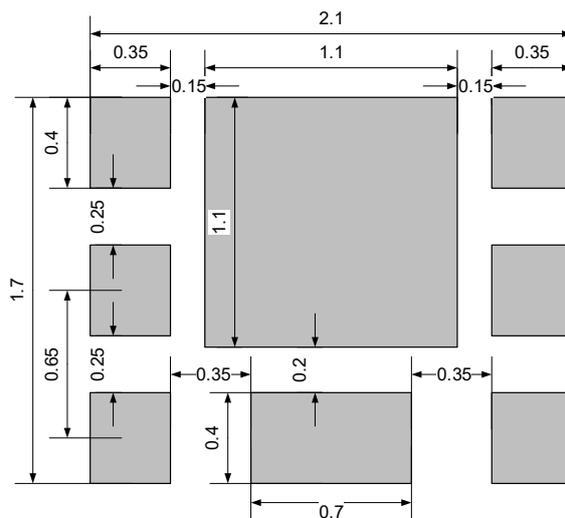
Ordering information

Device	Package	MSL	Reel	Shipping
PSM6N30V20	DFN2020-6L	3	7"	3000 / Tape & Reel

## Product Dimension (DFN2020-6L)



Dim	Millimeters	
	Min	Max
A	0.50	0.60
A1	0.00	0.05
A2	0.152 Ref.	
b	0.25	0.35
D	1.90	2.10
E	1.90	2.10
D1	0.80	1.00
E1	0.80	1.00
D2	0.25	0.35
E2	0.46	0.66
e	0.65 Ref.	
H	0.30 Ref.	
K	0.42 Ref.	
K1	0.25 Ref.	
K2	0.35 Ref.	
L	0.25	0.35
L1	0.20 Ref.	
L2	0.25 Ref.	



Unit: mm

Suggested PCB Layout

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